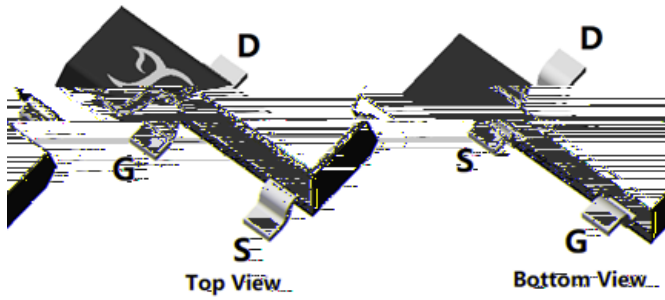
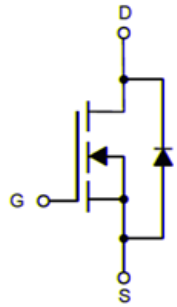




N-Channel Enhancement Mode Field Effect Transistor



SOT-23



Product Summary

V_{DS}	50V
I_D	600mA
$R_{DS(ON)}$ (at $V_{GS}=10V$)	1100m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	1200m

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface TTL/CMOS

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-source Voltage	V_{DS}	50	V	
Gate-source Voltage	V_{GS}	± 20	V	
Drain Current	I_D	$T_A=25$	600	mA
		$T_A=100$	380	
Pulsed Drain Current ^A	I_{DM}	2	A	
Total Power Dissipation ^B	P_D	$T_A=25$	830	mW
		$T_A=100$	330	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150		

Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^C	R_{JA}	120	150	$^{\circ}W$

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS138B	F2	138B.	3000	30000	120000	7" reel



BSS138B

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	50	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=50V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8	1.2	1.6	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=300mA$	-	680	1100	m
		$V_{GS}=4.5V, I_D=200mA$	-	750	1200	
Diode Forward Voltage	V_{SD}	$I_S=300mA, V_{GS}=0V$	-	-	1.2	V
Gate resistance	R					



Typical Electrical and Thermal Characteristics Diagrams

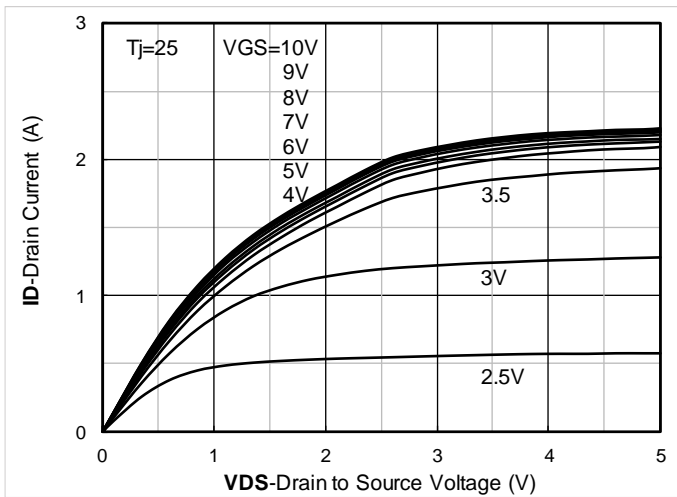


Figure 1. Output Characteristics

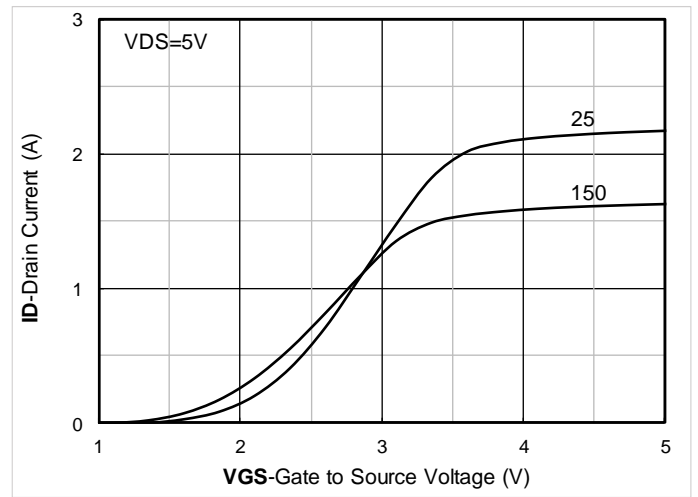


Figure 2. Transfer Characteristics

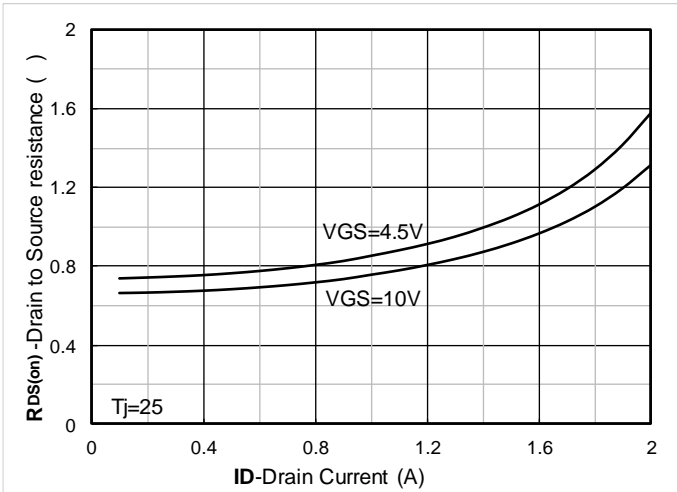


Figure 7. RDS(on) VS Drain Current

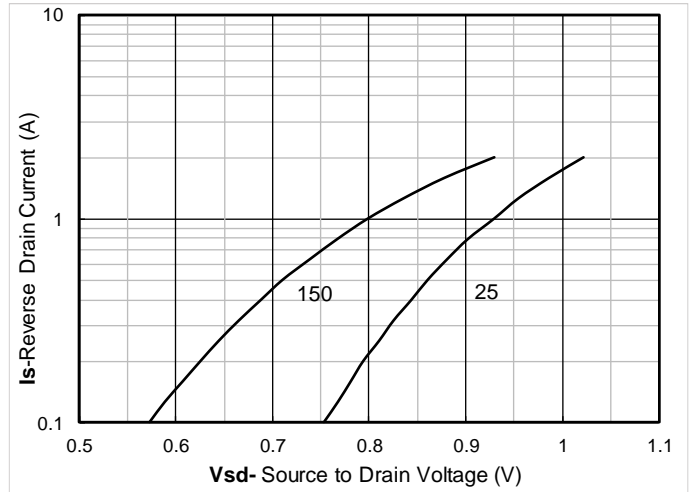


Figure 8. Forward characteristics of reverse diode

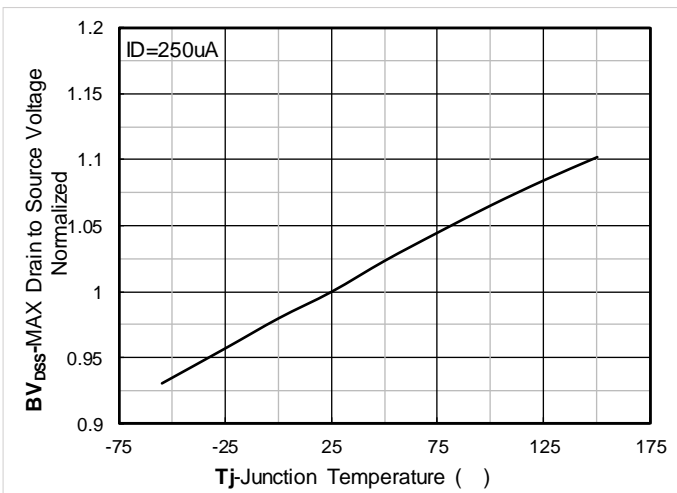


Figure 9. Normalized breakdown voltage

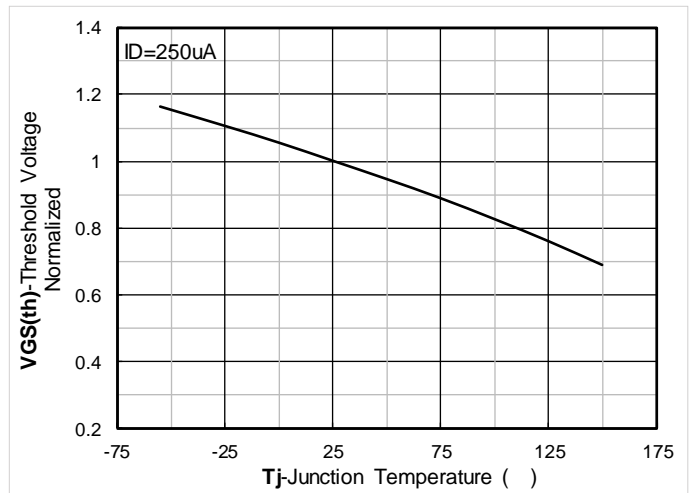


Figure 10. Normalized Threshold voltage

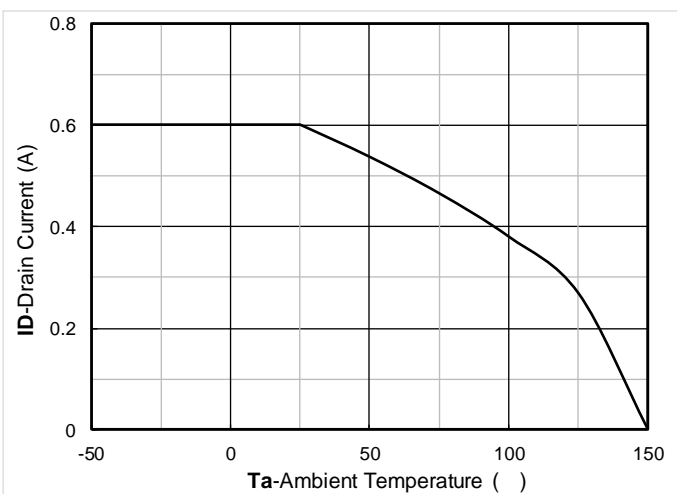


Figure 11. Current dissipation

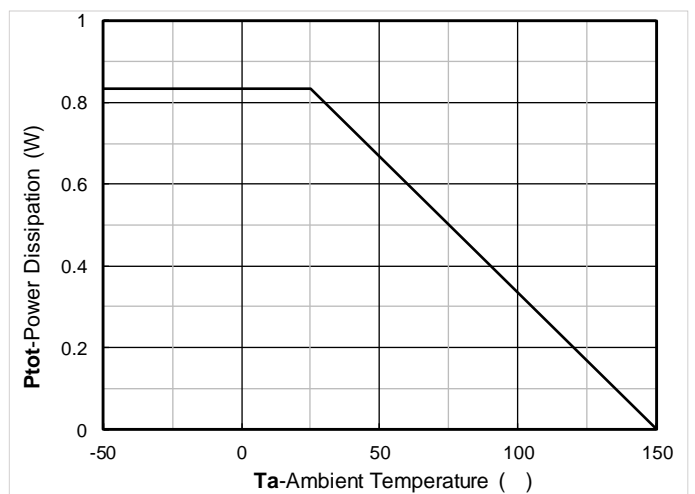


Figure 12. Power dissipation

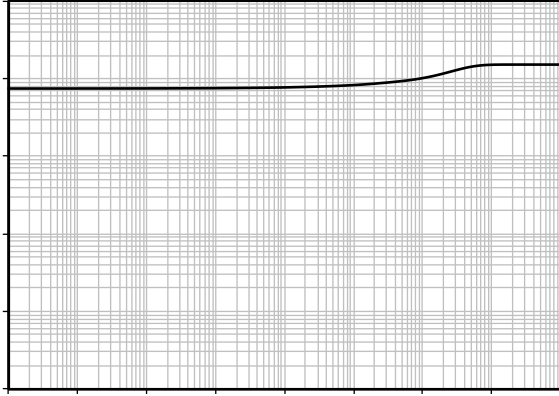


Figure 13. Maximum Transient Thermal Impedance

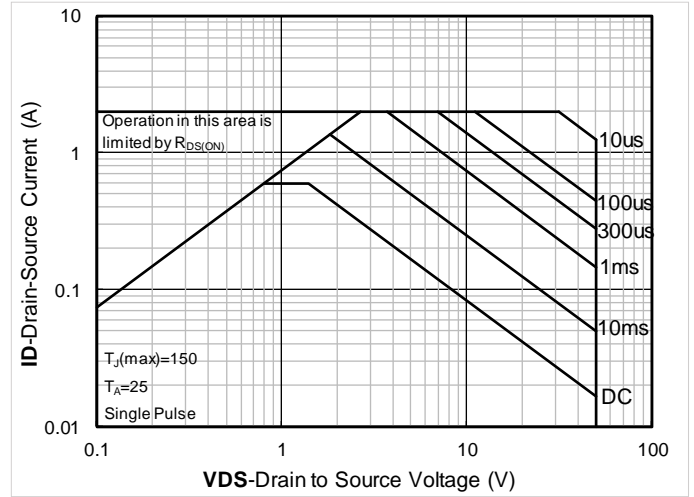


Figure 14. Safe Operation Area

Test Circuits & Waveforms

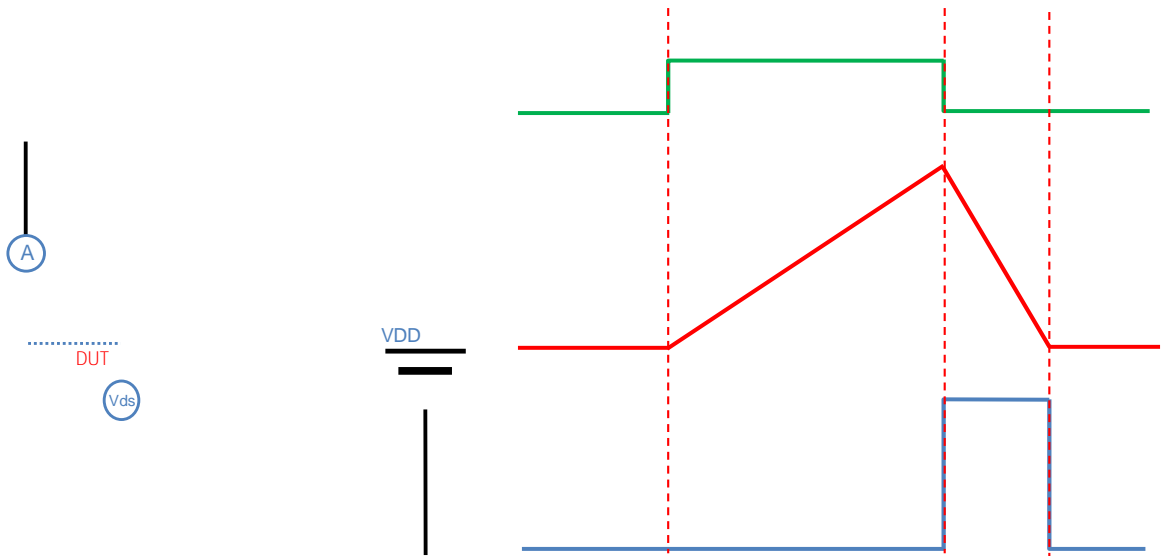


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

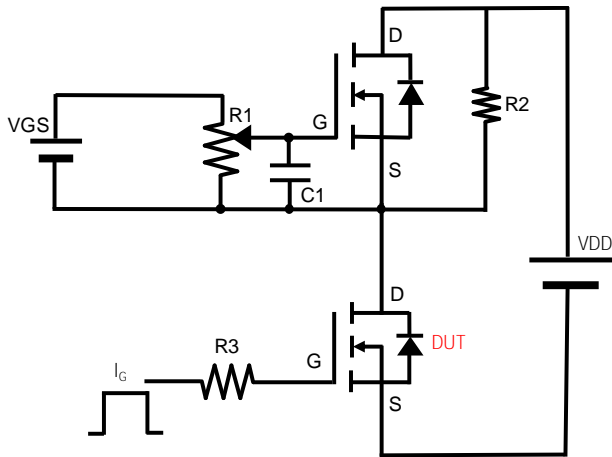


Figure B. Gate Charge Test Circuit & Waveform

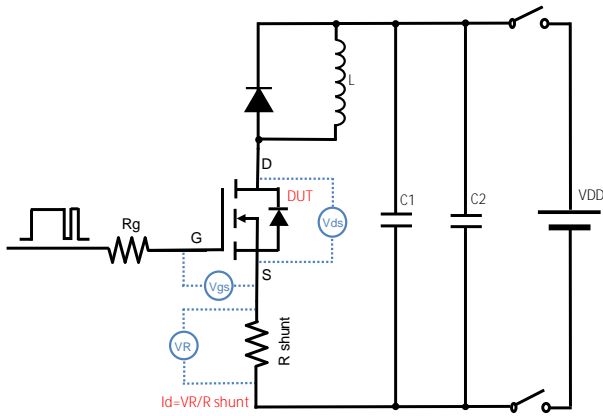


Figure C. Resistive Switching Test Circuit & Waveform

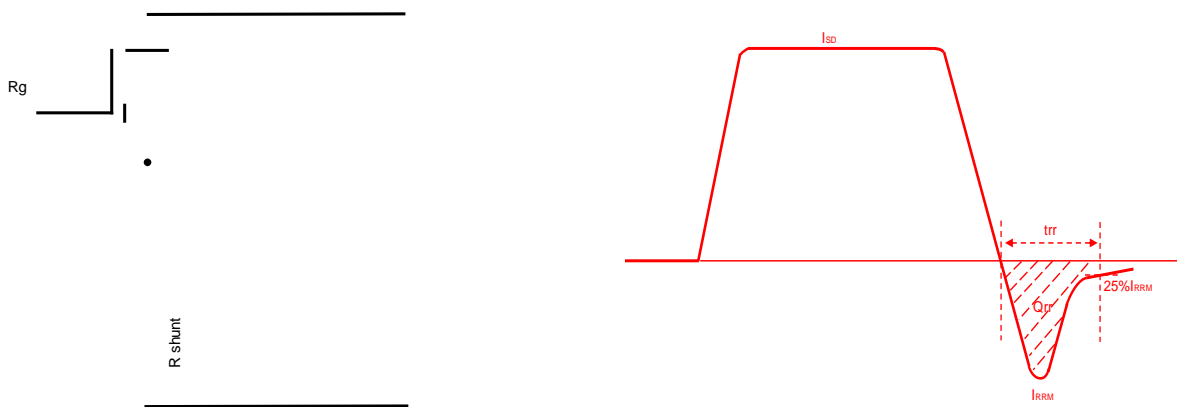
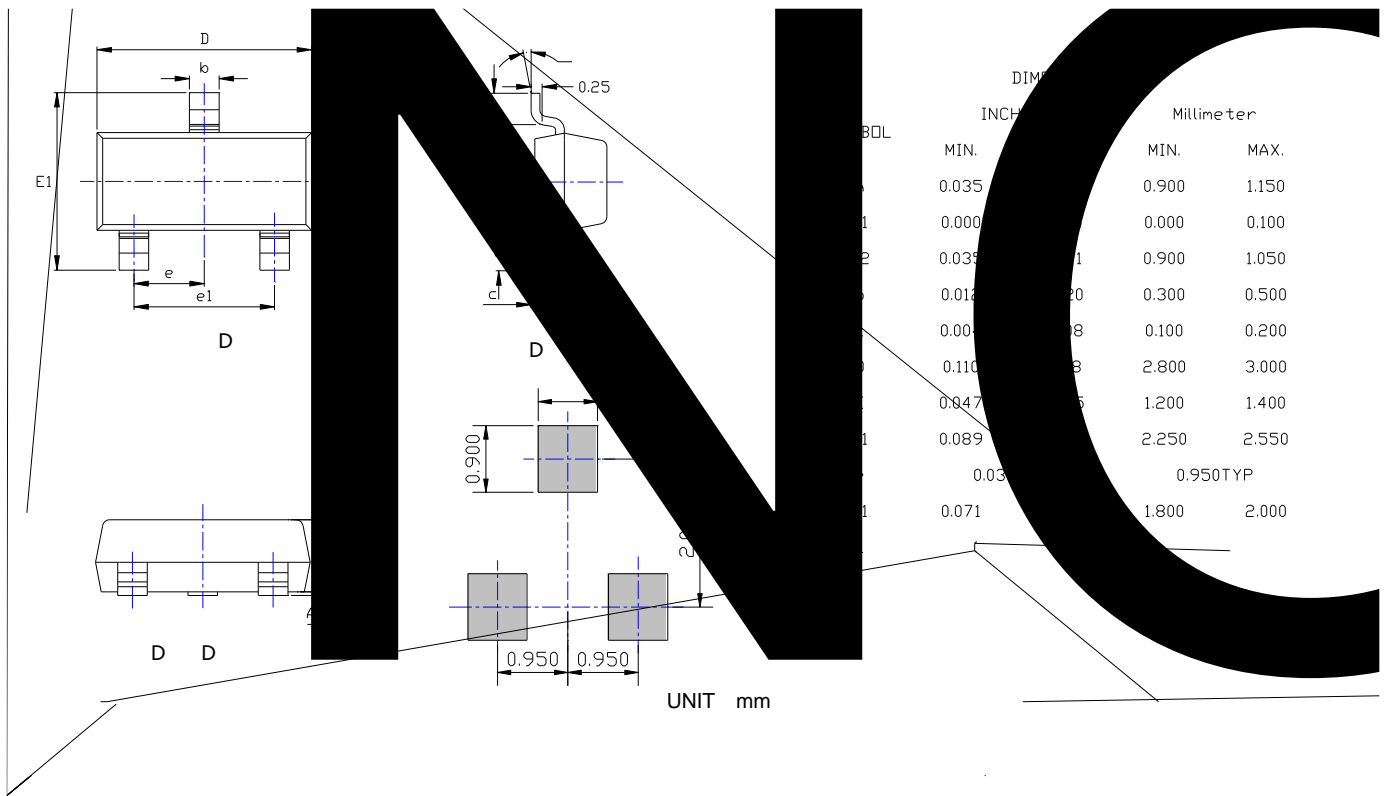


Figure D. Diode Recovery Test Circuit & Waveform



BSS138B

SOT-23 Package information





BSS138B

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